

Silicon PNP Power Transistors

2SB1145

DESCRIPTION

- With TO-220F package
- High DC current gain.
- DARLINGTON
- Low collector saturation voltage

APPLICATIONS

- For high current driver and power driver applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

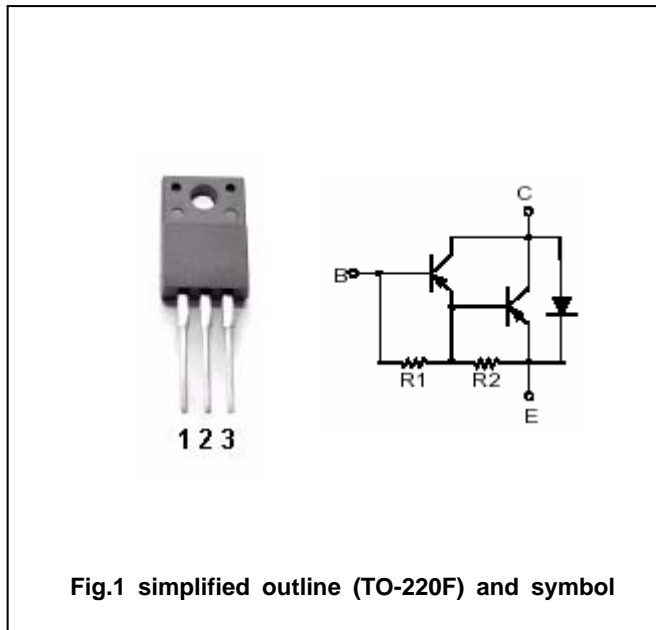


Fig.1 simplified outline (TO-220F) and symbol

Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-120	V
V_{CEO}	Collector-emitter voltage	Open base	-120	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-3	A
I_{CM}	Collector current-peak		-5	A
P_C	Collector dissipation	$T_C=25$	20	W
		$T_a=25$	2	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-100 μ A; I _E =0	-120			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-5mA; I _B =0	-120			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1.5A; I _B =-3mA			-1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-1.5A; I _B =-3mA			-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-120V; I _E =0			-50	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-3.0	mA
h _{FE}	DC current gain	I _C =-1.5A; V _{CE} =-3V	2000			

